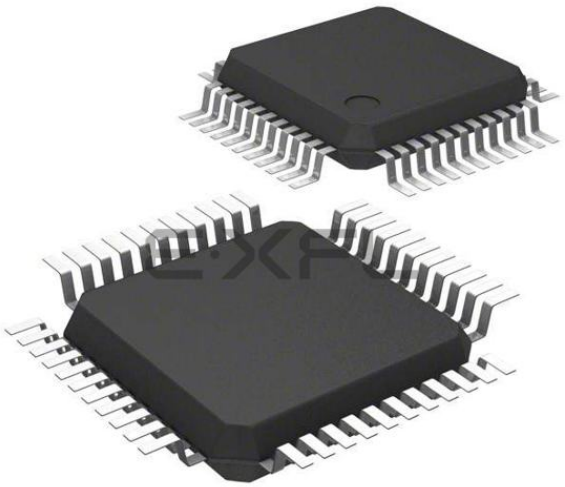
Renesas Electronics America Inc - R5F104FCAFP#X0 Datasheet



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What is "Embedded - Microcontrollers"?

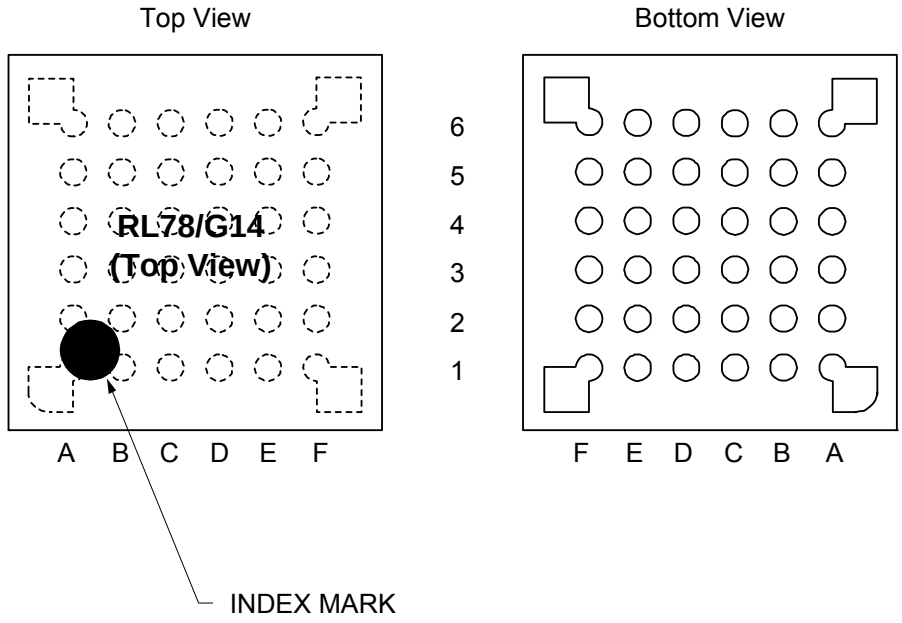
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fcafp-x0

1.3.3 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	A	B	C	D	E	F	
6	P60/SCLA0	VDD	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62/$\overline{SSI00}$	P61/SDAA0	VSS	REGC	$\overline{RESET}$	P120/ANI19/ VCOUT0 Note	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/TRDIOD0/ (SCLA0)	P31/TI03/TO03/ INTP4/PCLBUZ0/ (TRJIO0)	P00/TI00/TxD1/ TRGCLKA/ (TRJO0)	P01/TO00/ RxD1/TRGCLKB/ TRJIO0	4
3	P50/INTP1/ SI00/RxD0/ TOOLRxD/ SDA00/TRGIOA/ (TRJO0)	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ TRDIOB0/ (SDAA0)	P22/ANI2/ ANO0 Note	P20/ANI0/ AVREFP	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK00/SCL00/ TRJO0	P16/TI01/TO01/ INTP5/TRDIOC0/ IVREF0 Note/ (RXD0)	P12/SO11/ TRDIOB1/ IVREF1 Note	P11/SI11/ SDA11/ TRDIOC1	P24/ANI4	P23/ANI3/ ANO1 Note	2
1	P51/INTP2/ SO00/TxD0/ TOOLTxD/ TRGIOB	P17/TI02/TO02/ TRDIOA0/ TRDCLK/ IVCMP0 Note/ (TXD0)	P13/TxD2/ SO20/TRDIOA1/ IVCMP1 Note	P10/SCK11/ SCL11/ TRDIOD1	P147/ANI18/ VCOUT1 Note	P25/ANI5	1
	A	B	C	D	E	F	

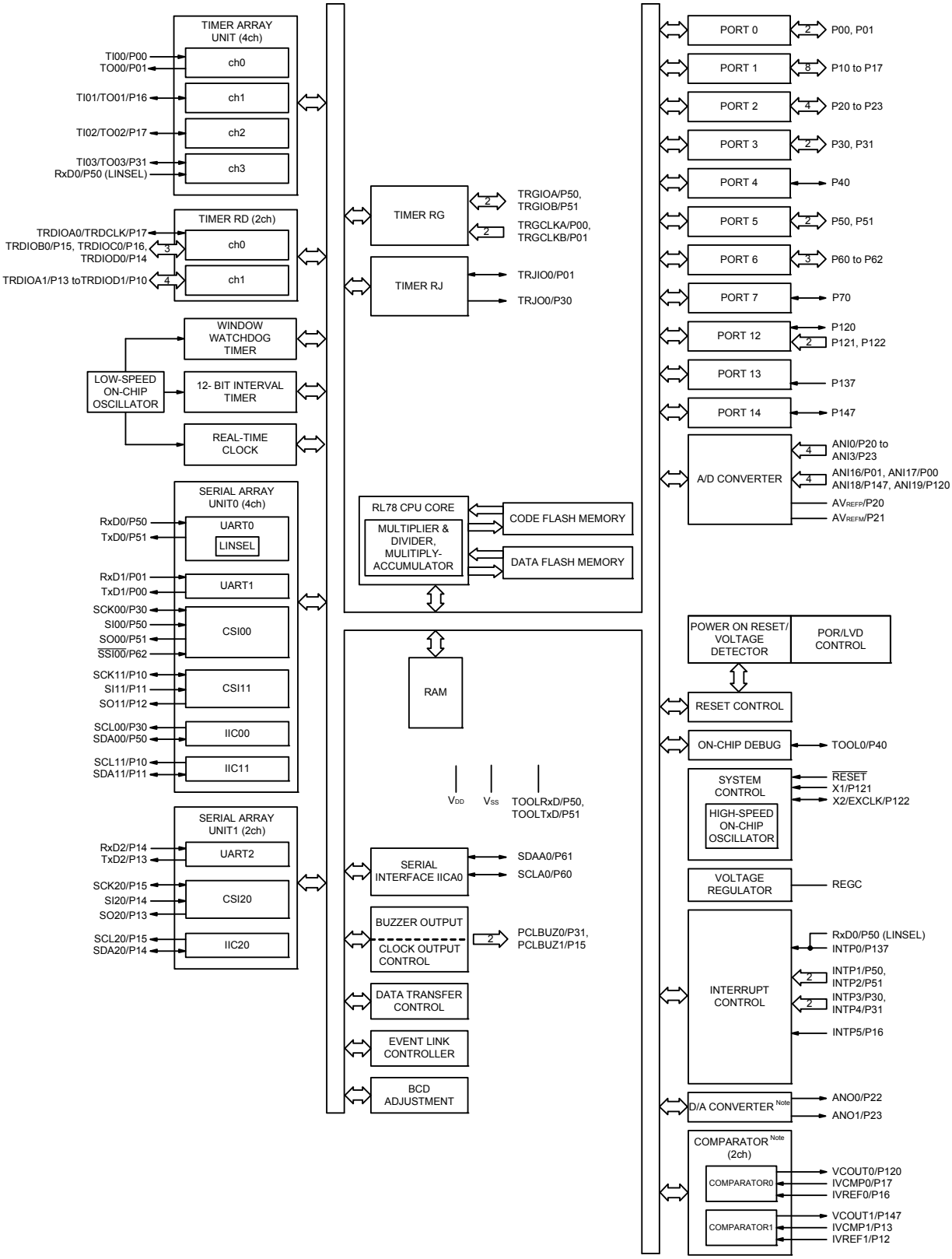
Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

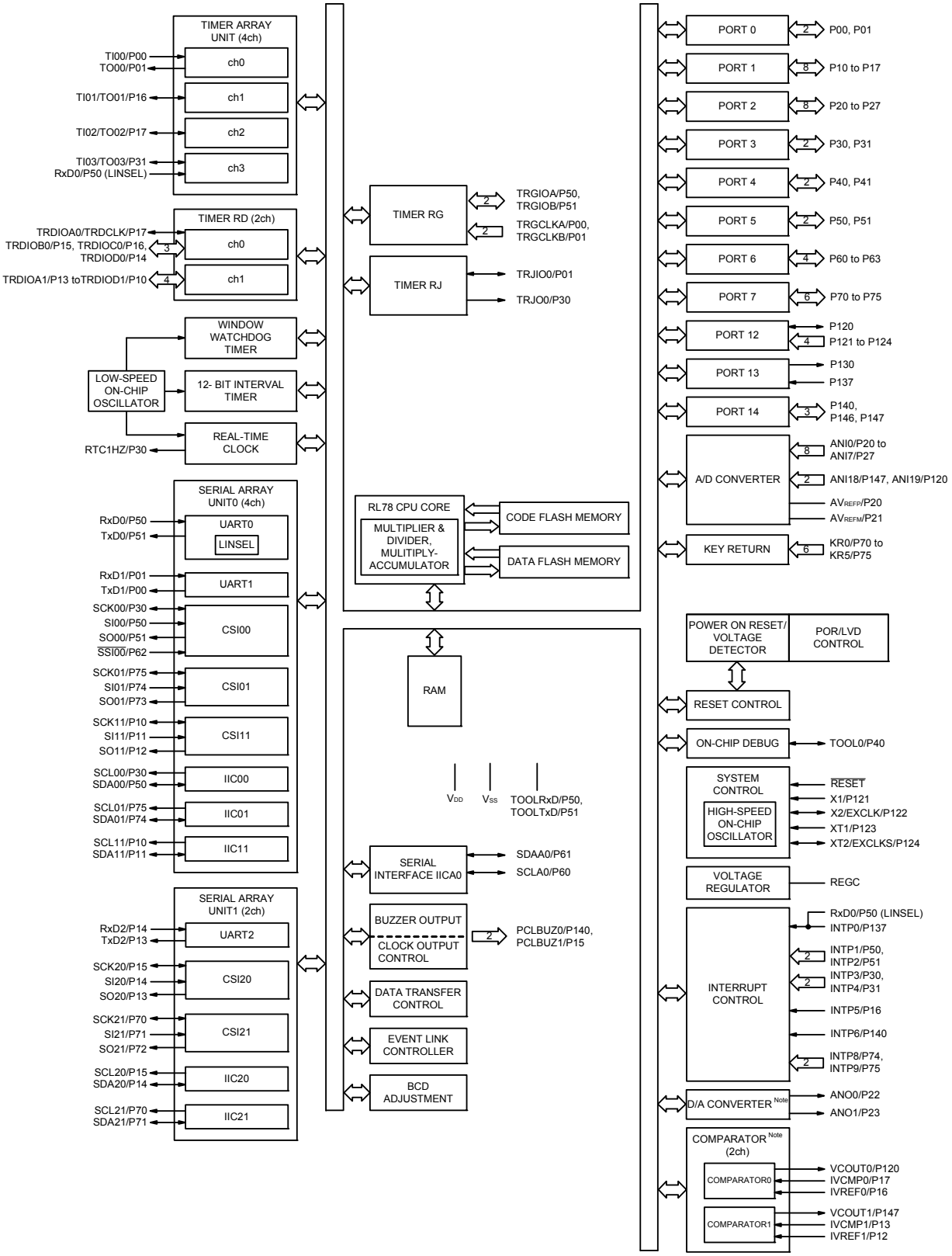
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.5.2 32-pin products



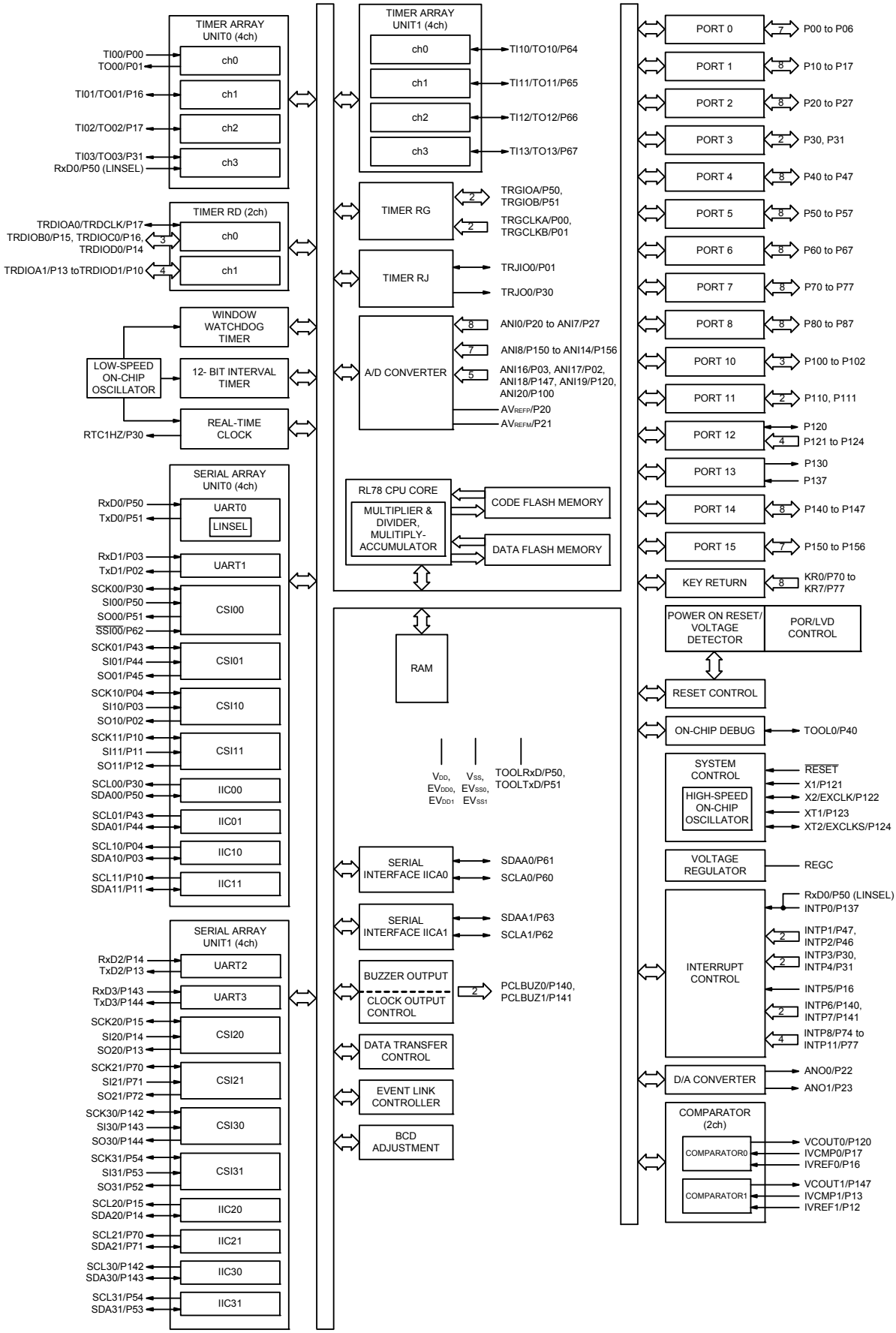
Note Mounted on the 96 KB or more code flash memory products.

1.5.6 48-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.10 100-pin products



[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)
Code flash memory (KB)		96 to 128	96 to 128	96 to 128	96 to 192
Data flash memory (KB)		8	8	8	8
RAM (KB)		12 to 16 Note	12 to 16 Note	12 to 16 Note	12 to 20 Note
Address space		1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
Subsystem clock		—			XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)			
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)			
		—			30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.			
I/O port	Total	26	28	32	36
	CMOS I/O	21	22	26	28
	CMOS input	3	3	3	5
	CMOS output	—	—	—	—
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels			
	RTC output	—			1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)

(**Note** is listed on the next page.)

[80-pin, 100-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		80-pin	100-pin
		R5F104Mx (x = K, L)	R5F104Px (x = K, L)
Code flash memory (KB)		384 to 512	384 to 512
Data flash memory (KB)		8	8
RAM (KB)		32 to 48 Note	32 to 48 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)	
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)	
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)	

Note In the case of the 48 KB, this is about 47 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			70.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			15.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			9.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			4.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			80.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			35.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			20.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	I_{OL2}	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 5.5 V			5.0	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EV_{SS0}, EV_{SS1}, and V_{SS} pins.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA
Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≈ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.93	3.32	mA
					V_{DD} = 3.0 V		0.93	3.32	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.5	2.63	
					V_{DD} = 3.0 V		0.5	2.63	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.72	2.60	
					V_{DD} = 3.0 V		0.72	2.60	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.42	2.03	
					V_{DD} = 3.0 V		0.42	2.03	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.39	1.50	
					V_{DD} = 3.0 V		0.39	1.50	
			LS (low-speed main) mode Note 7	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		270	800	µA
					V_{DD} = 2.0 V		270	800	
			LV (low-voltage main) mode Note 7	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		450	755	µA
					V_{DD} = 2.0 V		450	755	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.31	1.69	mA
					Resonator connection		0.41	1.91	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.31	1.69	
					Resonator connection		0.41	1.91	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.21	0.94	
					Resonator connection		0.26	1.02	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.21	0.94	
					Resonator connection		0.26	1.02	
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		110	610	µA
					Resonator connection		150	660	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		110	610	
					Resonator connection		150	660	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.31		µA
					Resonator connection		0.50		
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.38	0.76	
					Resonator connection		0.57	0.95	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.47	3.59	
					Resonator connection		0.70	3.78	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.80	6.20	
					Resonator connection		1.00	6.39	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		1.65	10.56	
					Resonator connection		1.84	10.75	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.19		µA
			T_A = +25°C				0.30	0.59	
			T_A = +50°C				0.41	3.42	
			T_A = +70°C				0.80	6.03	
			T_A = +85°C				1.53	10.39	

(**Notes** and **Remarks** are listed on the next page.)

(4) Peripheral Functions (Common to all products)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.22		μA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV_{REFP} = V_{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		μA
D/A converter operating current	I_{DAC} Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating current	I_{CMP} Notes 1, 12, 13	V_{DD} = 5.0 V, Regulator output voltage = 2.1 V	Window mode		12.5		μA
			Comparator high-speed mode		6.5		μA
			Comparator low-speed mode		1.7		μA
		V_{DD} = 5.0 V, Regulator output voltage = 1.8 V	Window mode		8.0		μA
			Comparator high-speed mode		4.0		μA
			Comparator low-speed mode		1.3		μA
LVD operating current	I_{LVD} Notes 1, 7				0.08		μA
Self-programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		1.20	1.44	
		CSI/UART operation			0.70	0.84	
		DTC operation			3.10		

Note 1. Current flowing to V_{DD}.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

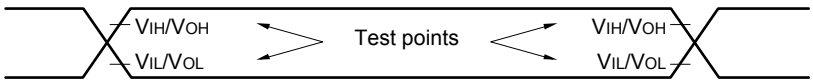
Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

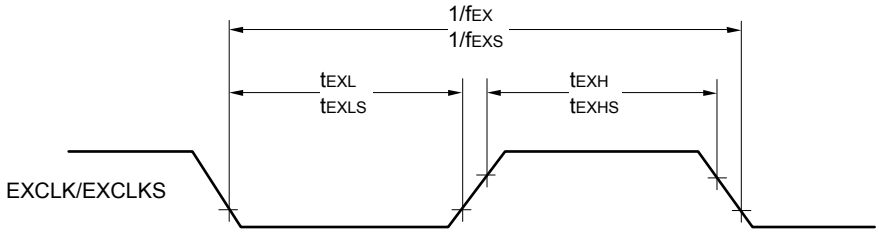
(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	t_{TDIH}, t_{TDIL}	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/f_{CLK}			ns
Timer RD forced cutoff signal input low-level width	t_{TDSIL}	P130/INTP0	2MHz < f_{CLK} ≤ 32 MHz	1			µs
			f_{CLK} ≤ 2 MHz	1/f_{CLK} + 1			
Timer RG input high-level width, low-level width	t_{TGIH}, t_{TGIL}	TRGIOA, TRGIOB		2.5/f_{CLK}			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	f_{TO}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V			16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V			8	MHz
			1.8 V ≤ EV_{DD0} < 2.7 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EV_{DD0} ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V			16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V			8	MHz
			1.8 V ≤ EV_{DD0} < 2.7 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0	1.6 V ≤ V_{DD} ≤ 5.5 V	1			µs
		INTP1 to INTP11	1.6 V ≤ EV_{DD0} ≤ 5.5 V	1			µs
Key interrupt input low-level width	t_{KR}	KR0 to KR7	1.8 V ≤ EV_{DD0} ≤ 5.5 V	250			ns
			1.6 V ≤ EV_{DD0} < 1.8 V	1			µs
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			µs

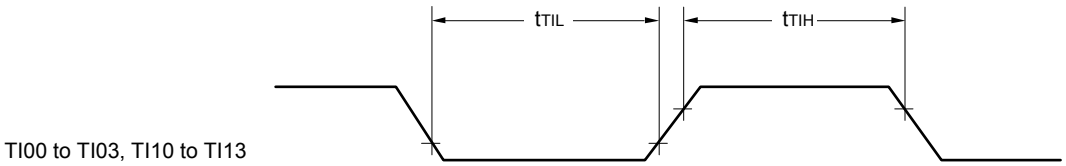
AC Timing Test Points

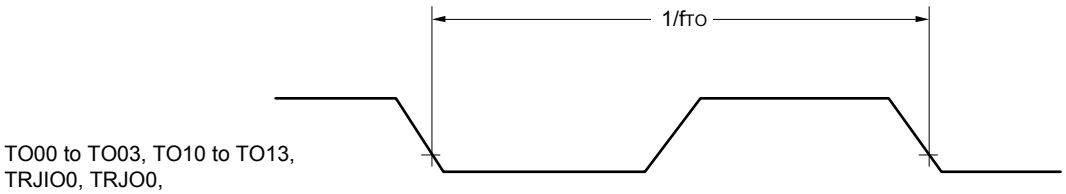


External System Clock Timing



TI/TO Timing

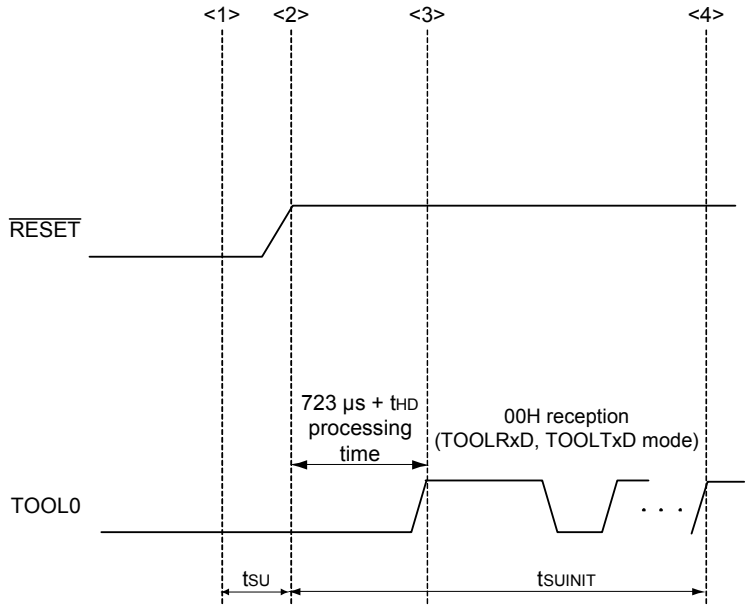




2.10 Timing of Entry to Flash Memory Programming Modes

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.
<2> The external reset ends (POR and LVD reset must end before the external reset ends).
<3> The TOOL0 pin is set to the high level.
<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.
t_{SU}: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
t_{HD}: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

Note 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

<R>

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.93	5.16	mA
					V_{DD} = 3.0 V		0.93	5.16	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.5	4.47	
					V_{DD} = 3.0 V		0.5	4.47	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.72	4.08	
					V_{DD} = 3.0 V		0.72	4.08	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.42	3.51	
					V_{DD} = 3.0 V		0.42	3.51	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.39	2.38	
					V_{DD} = 3.0 V		0.39	2.38	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.31	2.83	mA
					Resonator connection		0.41	2.92	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.31	2.83	
					Resonator connection		0.41	2.92	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.21	1.46	
					Resonator connection		0.26	1.57	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.21	1.46	
					Resonator connection		0.26	1.57	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.31	0.76	µA
					Resonator connection		0.50	0.95	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.38	0.76	
					Resonator connection		0.57	0.95	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.47	3.59	
					Resonator connection		0.70	3.78	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.80	6.20	
					Resonator connection		1.00	6.39	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		1.65	10.56	
					Resonator connection		1.84	10.75	
				f_{SUB} = 32.768 kHz Note 5, T_A = +105°C	Square wave input		8.00	65.7	
					Resonator connection		8.00	65.7	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.19	0.63	µA
			T_A = +25°C				0.30	0.63	
			T_A = +50°C				0.41	3.47	
			T_A = +70°C				0.80	6.08	
			T_A = +85°C				1.53	10.44	
			T_A = +105°C				6.50	67.14	

(**Notes** and **Remarks** are listed on the next page.)

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

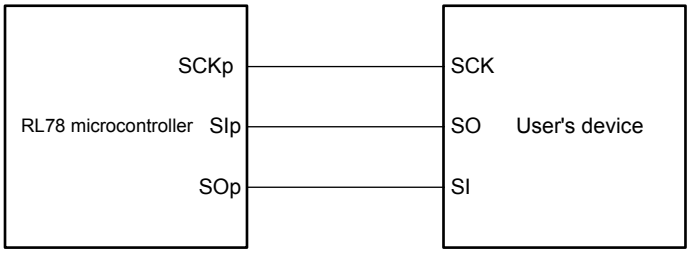
(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ EV_{DD0} ≤ 5.5 V	240		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	400		ns
		DAPmn = 1	2.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 240		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 400		ns
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 240		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 400		ns
		DAPmn = 1	2.7 V ≤ EV_{DD0} ≤ 5.5 V	240		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	400		ns

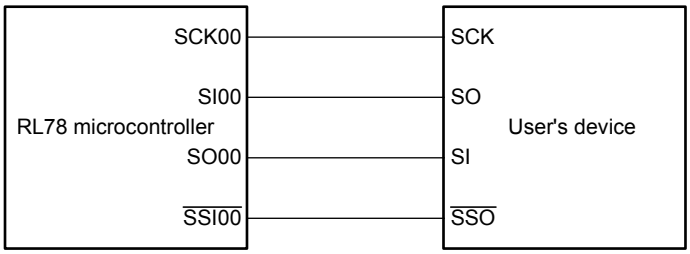
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)

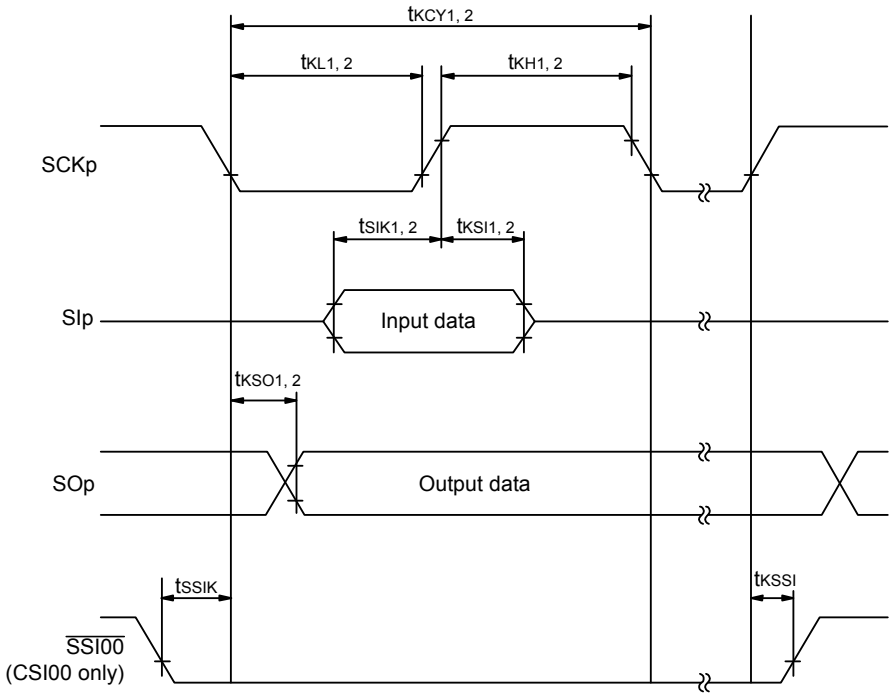


CSI mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))

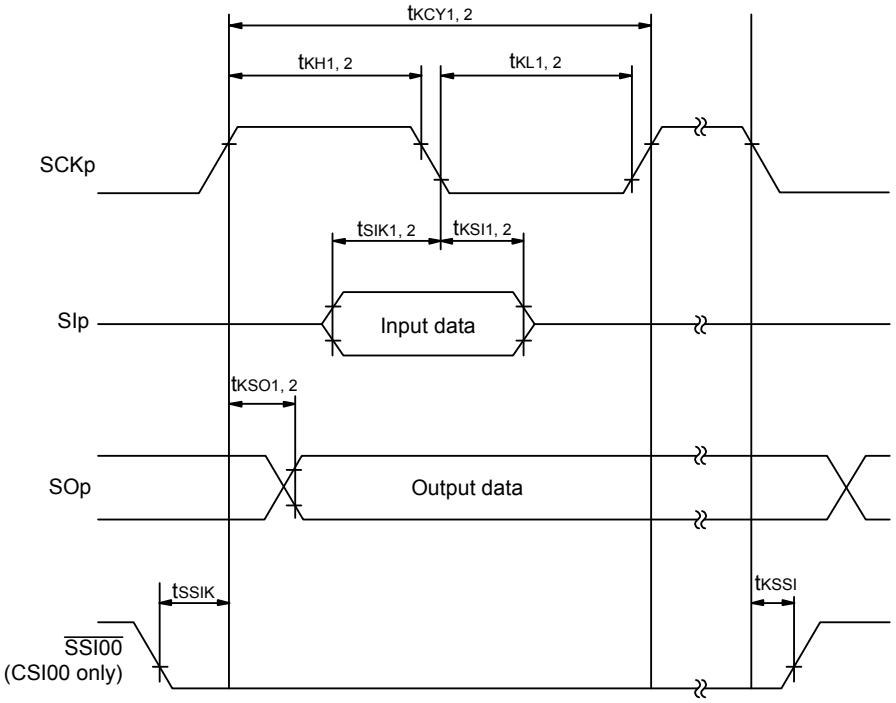


Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

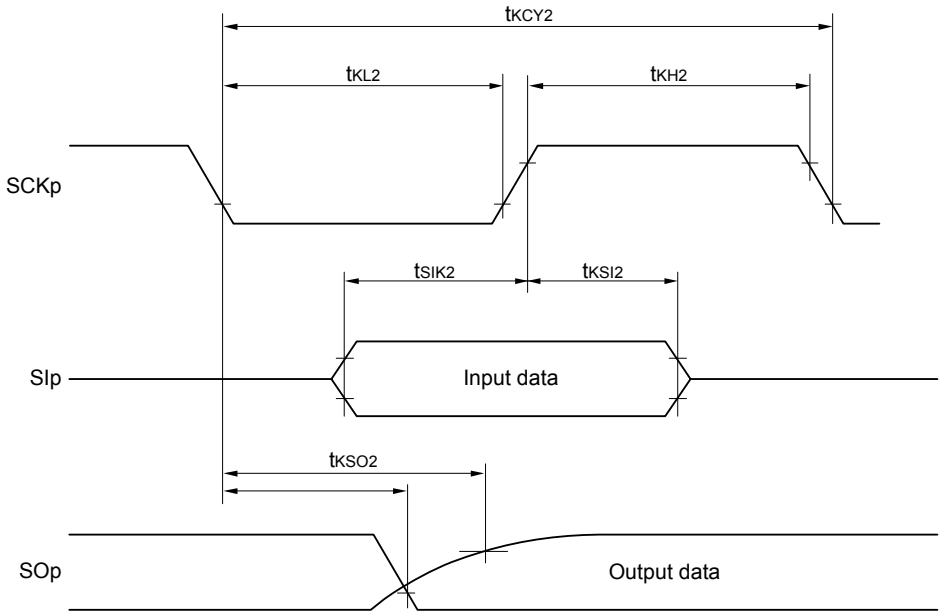


CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)

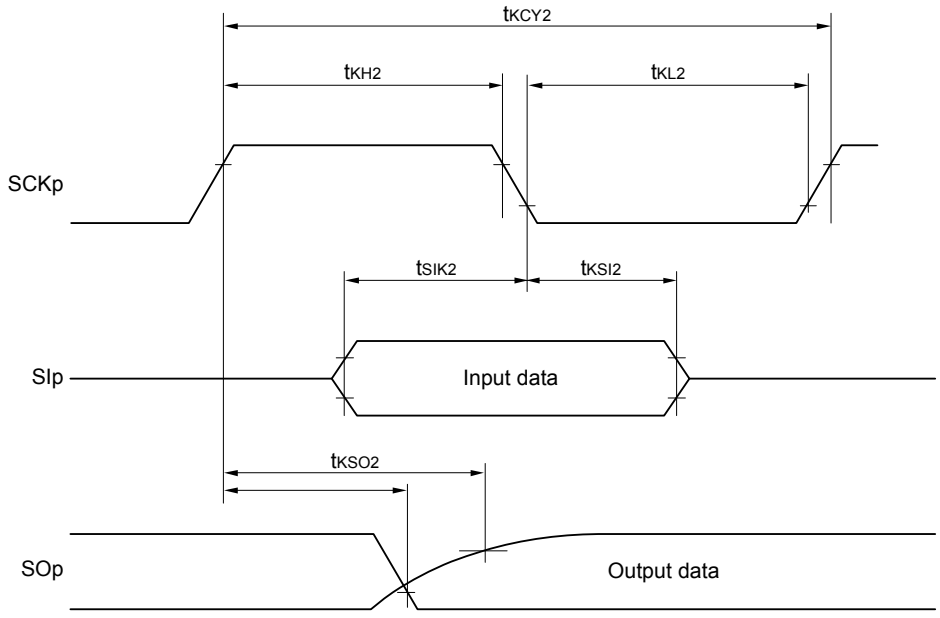


Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.
Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

3.6.4 Comparator

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		EV_{DD0} - 1.4	V
	Ivcmp			-0.3		EV_{DD0} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	µs
			Comparator high-speed mode, window mode			2.0	µs
			Comparator low-speed mode, standard mode		3.0	5.0	µs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode, window mode			0.76 V_{DD}		V
Low-electric-potential reference voltage	VTW-	Comparator high-speed mode, window mode			0.24 V_{DD}		V
Operation stabilization wait time	t_{CMP}			100			µs
Internal reference voltage Note	V_{BGR}	2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode		1.38	1.45	1.50	V

Note Not usable in sub-clock operation or STOP mode.

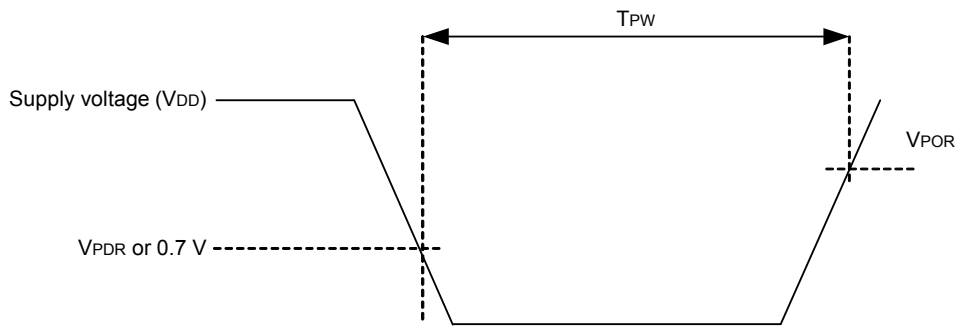
3.6.5 POR circuit characteristics

(T_A = -40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	V_{POR}	Voltage threshold on V_{DD} rising	1.45	1.51	1.57	V
	V_{PDR}	Voltage threshold on V_{DD} falling Note 1	1.44	1.50	1.56	V
Minimum pulse width Note 2	T_{PW}		300			µs

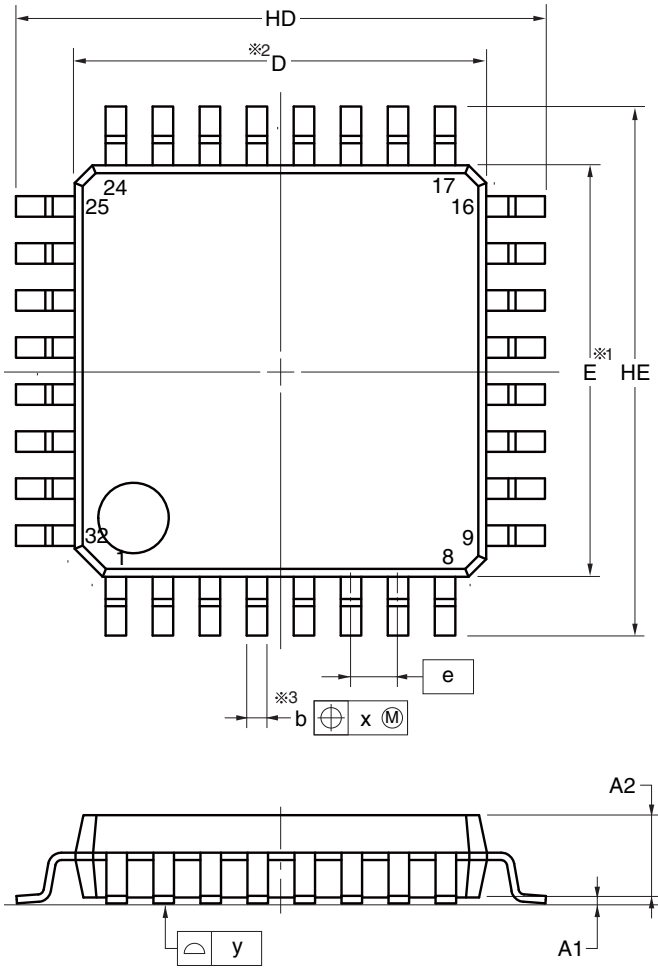
Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.

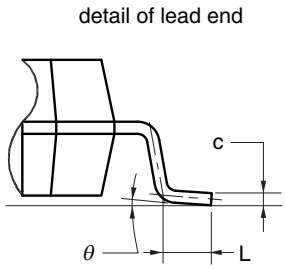
Note 2. Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP
R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP
R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2





(UNIT:mm)

ITEM	DIMENSIONS
D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
A	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
c	0.145±0.055
L	0.50±0.20
θ	0° to 8°
e	0.80
x	0.20
y	0.10

NOTE

1.Dimensions "※1" and "※2" do not include mold flash.

2.Dimension "※3" does not include trim offset.

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.